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(54) **METHOD FOR PREVENTING SHORT CIRCUIT BETWEEN METAL WIRES IN ORGANIC LIGHT EMITTING DIODE DISPLAY DEVICE**

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CPC **H01L 51/56** (2013.01); **H01L 27/3276** (2013.01); **H01L 2251/5392** (2013.01); **H01L 2227/323** (2013.01)

(58) **Field of Classification Search**

CPC H01L 51/56; H01L 27/3276; H05B 33/06

USPC 257/40–48, 642–643, 759, 257/E51.001–E51.052, E25.008–E25.009; 438/46

See application file for complete search history.

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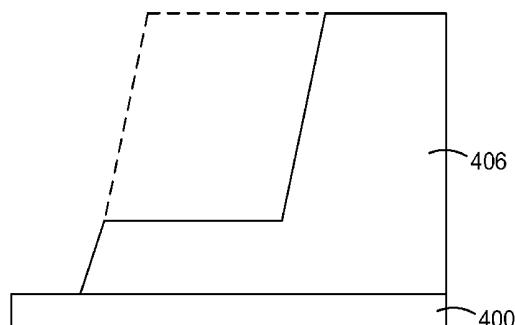
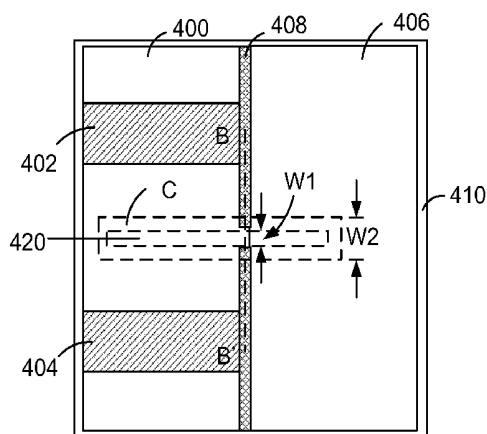
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(57) **ABSTRACT**

Disclosed is a method for preventing a short circuit between metal wires in an organic light emitting diode display device. The method includes: forming an inorganic layer on a substrate; forming a metal layer including two metal wires on the inorganic layer; forming an organic layer on the two metal wires; forming an indium tin oxide layer on the organic layer; coating a photoresist layer; performing an exposure step by utilizing a photo mask having a transparent area, an opaque material disposed in the transparent area, wherein a width of the opaque material is less than a width of the transparent area; performing a development step to the photoresist layer; and performing an etching step to remove a part of the indium tin oxide layer and a part of the organic layer. The present invention can prevent the short circuit between the metal wires.

16 Claims, 7 Drawing Sheets



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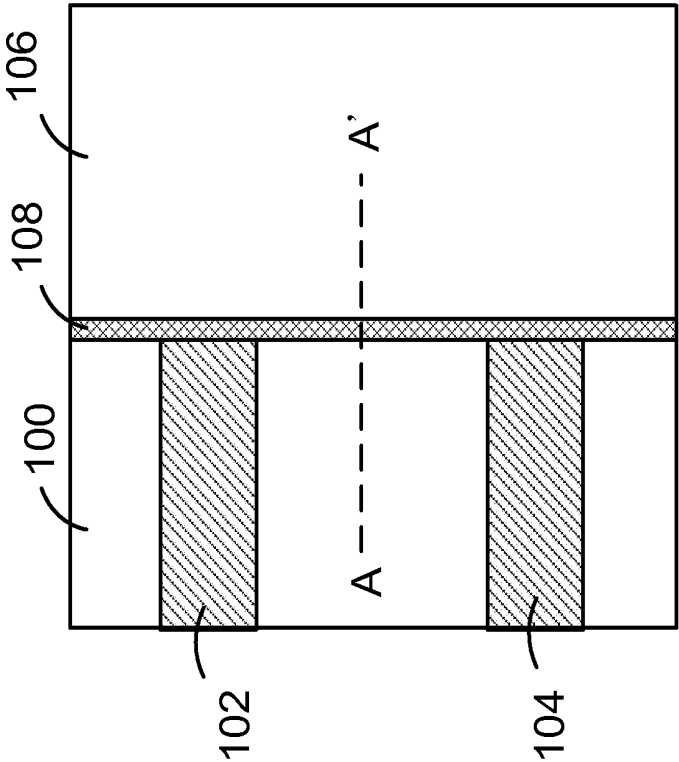


FIG. 1 (PRIOR ART)

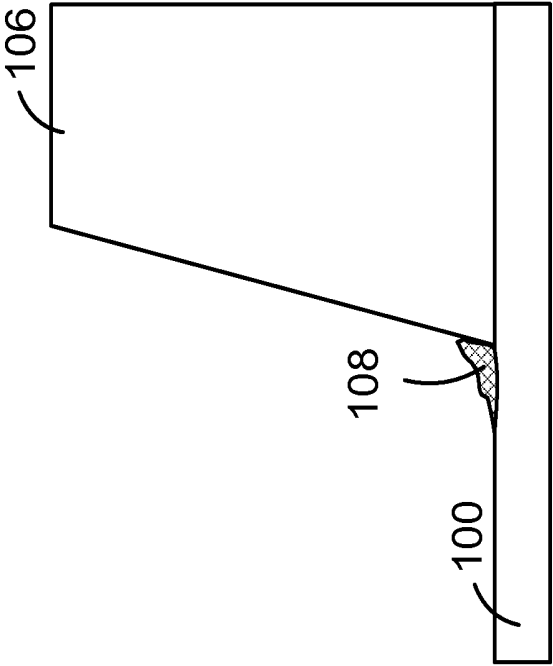


FIG. 2 (PRIOR ART)

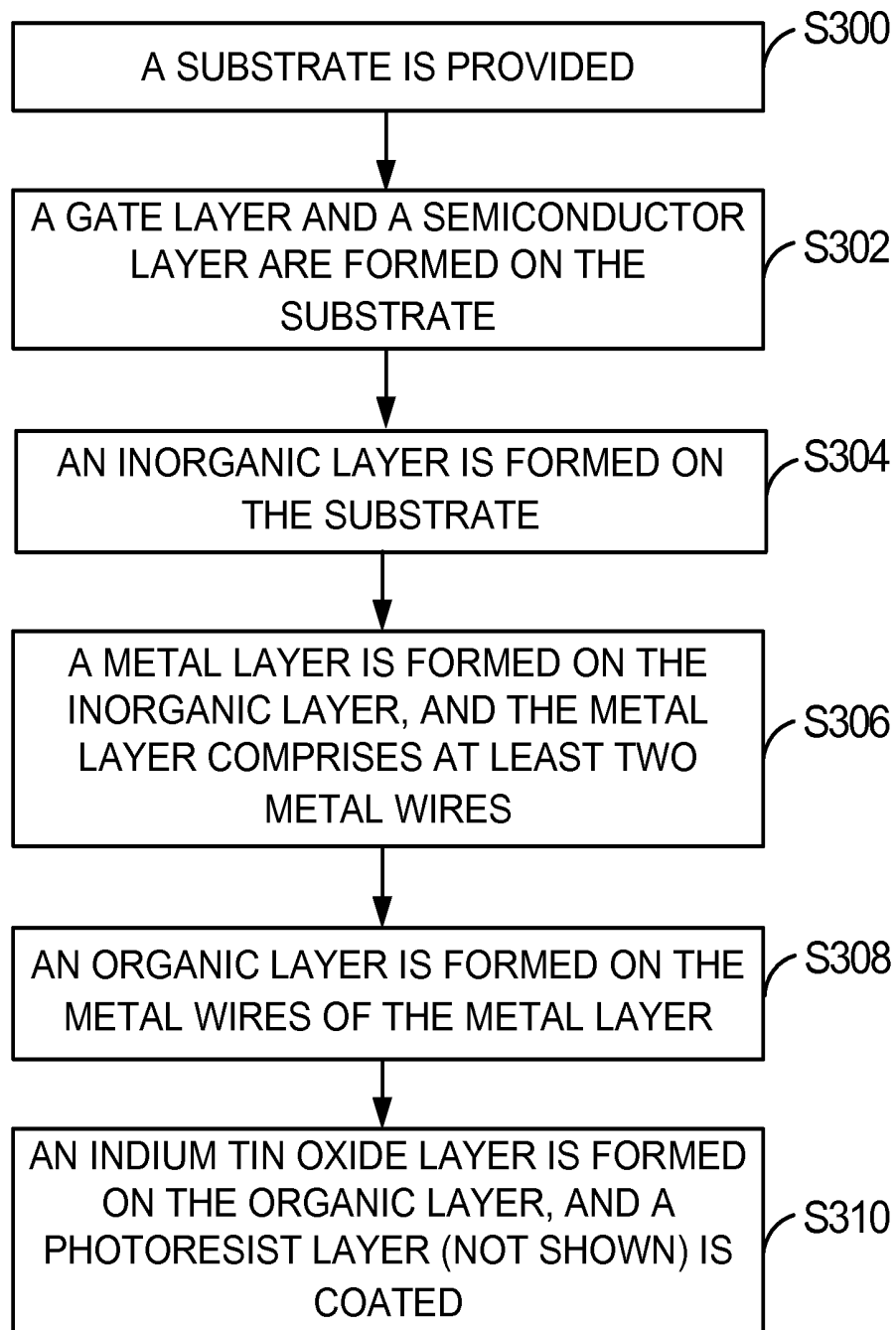


FIG. 3

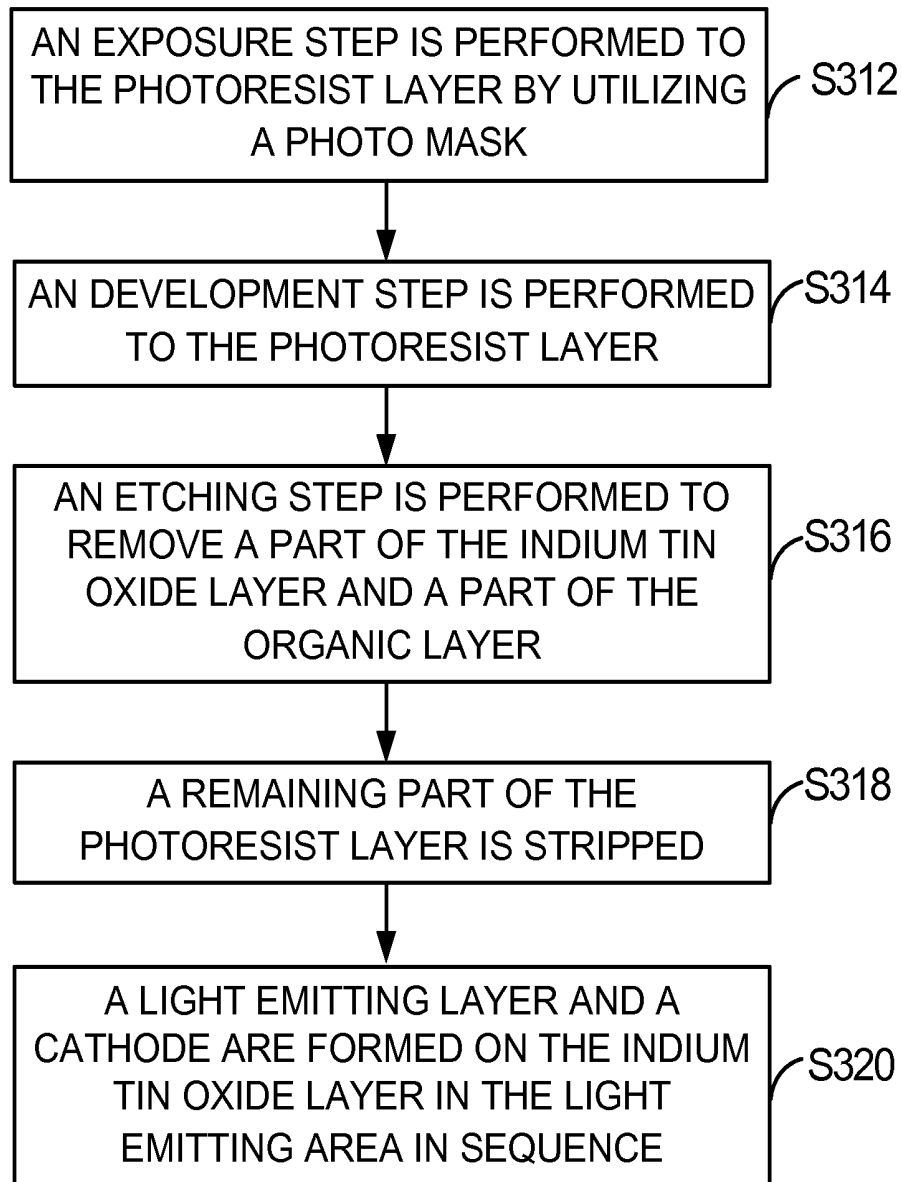


FIG. 3 (CONTINUED)

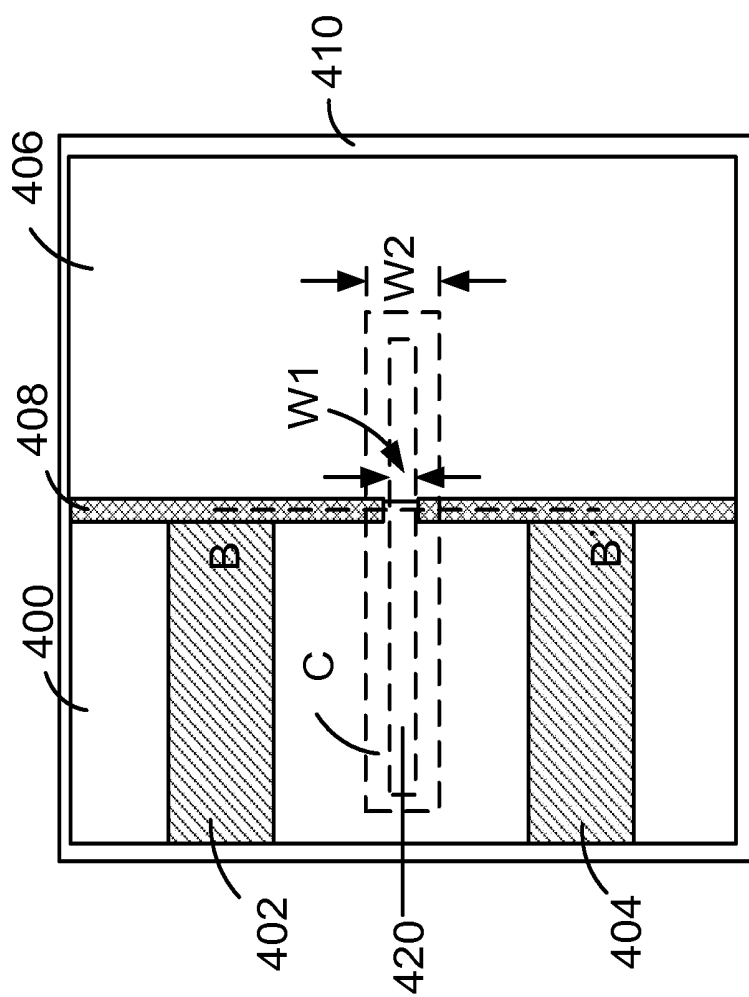


FIG. 4

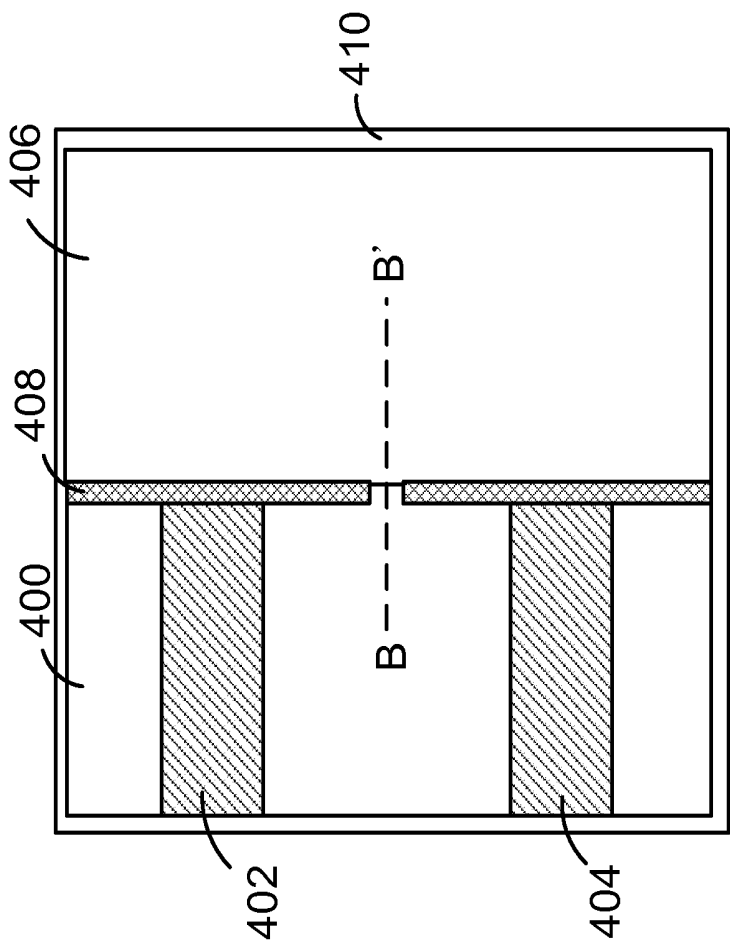


FIG. 5

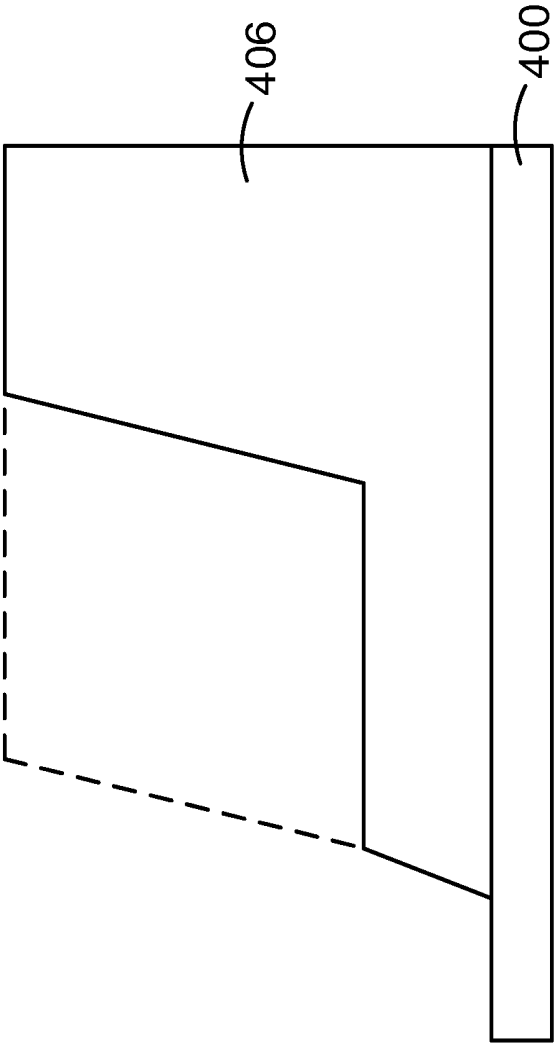


FIG. 6

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METHOD FOR PREVENTING SHORT CIRCUIT BETWEEN METAL WIRES IN ORGANIC LIGHT EMITTING DIODE DISPLAY DEVICE

BACKGROUND OF THE INVENTION

1. Field of the Invention

The present invention generally relates to an organic light emitting diode display device field, and more particularly to a method for preventing a short circuit between metal wires in an organic light emitting diode display device.

2. Description of Prior Art

An organic light emitting diode (OLED) display device has advantages of self-luminescent, lower power consumption, and wide viewing angle, and thus the organic light emitting diode display device is regarded as a display device with high development potential in the future.

Please refer to FIG. 1 and FIG. 2. FIG. 1 illustrates a top view of some elements of a conventional organic light emitting diode display device. FIG. 2 illustrates a cross-sectional view along a line AA' in FIG. 1.

In a manufacturing process of the organic light emitting diode display device, a plurality of thin film transistors which are served as switch elements are manufactured on a substrate (not shown) firstly, and then organic light emitting diodes which are served as light emitting elements are manufactured.

Manufacturing the thin film transistors and the light emitting diodes comprises the following steps. Firstly, a gate layer (not shown) and a semiconductor layer (not shown) are formed on the substrate (not shown). Then, an inorganic layer 100 is formed, and a metal layer is formed on the inorganic layer 100. The metal layer comprises metal wires 102 and 104 for respectively transmitting independent signals, that is, for transmitting different signals. An organic layer 106 is formed on the metal wires 102 and 104. An indium tin oxide (ITO) layer 108 is formed on the organic layer 106. The indium tin oxide layer 108 is utilized as an anode of an organic light emitting diode. Finally, a light emitting layer (now shown) and a cathode (not shown) are formed on the indium tin oxide layer 108.

However, in the manufacturing process of the organic light emitting diode display device, a photoresist layer (not shown) is formed on the indium tin oxide layer 108 after the indium tin oxide layer 108 is deposited. During an exposure step, a top of the organic layer 106 masks out a bottom of the indium tin oxide layer 108 because the organic layer 106 is too thick. Accordingly, the bottom of the indium tin oxide layer 106 cannot be irradiated by light. That is, the organic layer 106 generates shadowing effect. As a result, after an etching step is performed and the photoresist layer (not shown) is removed, a fraction of the indium tin oxide layer 108 is left as shown in FIG. 2, so that a short circuit occurs between the metal wires 102 and 104.

Consequently, there is a need to solve the problem that the short circuit occurs between the metal wires 102 and 104 because the fraction of the indium tin oxide layer 108 is left.

SUMMARY OF THE INVENTION

An objective of the present invention is to provide a method for preventing a short circuit between metal wires in an organic light emitting diode display device capable of solving the problem that a short circuit occurs between metal wires because an indium tin oxide layer is left.

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To solve the above-mentioned problem, a method for preventing a short circuit between metal wires in an organic light emitting diode display device provided by the present invention comprises:

- 5 forming an inorganic layer on a substrate;
- forming a metal layer on the inorganic layer, the metal layer comprising at least two metal wires;
- forming an organic layer on the two metal wires of the metal layer;
- 10 forming an indium tin oxide layer on the organic layer;
- coating a photoresist layer;
- performing an exposure step to the photoresist layer by utilizing a photo mask, the photo mask having a transparent area corresponding to a position between the two metal wires, an opaque material disposed in the transparent area, wherein a width of the transparent area of the photo mask is a resolution of the photo mask, and a width of the opaque material is less than the width of the transparent area of the photo mask;
- 15 performing a development step to the photoresist layer; and
- performing an etching step to remove a part of the indium tin oxide layer and a part of the organic layer.

After the step of performing the etching step to remove the part of the indium tin oxide layer and the part of the organic layer, the method for preventing the short circuit between the metal wires in the organic light emitting diode display device of the present invention further comprises a step of:

stripping a remaining part of the photoresist layer.

In the method for preventing the short circuit between the metal wires in the organic light emitting diode display device of the present invention, the width of the opaque material is less than 2 μm .

In the method for preventing the short circuit between the metal wires in the organic light emitting diode display device of the present invention, the width of the opaque material is preferably ranging from 1 μm to 2 μm .

In the method for preventing the short circuit between the metal wires in the organic light emitting diode display device of the present invention, the two metal wires are utilized as sources.

In the method for preventing the short circuit between the metal wires in the organic light emitting diode display device of the present invention, the two metal wires are utilized as drains.

In the method for preventing the short circuit between the metal wires in the organic light emitting diode display device of the present invention, the organic layer at least covers a part of the two metal wires.

In the method for preventing the short circuit between the metal wires in the organic light emitting diode display device of the present invention, the two metal wires are formed by a wet etching method.

To solve the above-mentioned problem, a method for preventing a short circuit between metal wires in an organic light emitting diode display device provided by the present invention comprises:

- forming an inorganic layer on a substrate;
- forming a metal layer on the inorganic layer, the metal layer comprising at least two metal wires;
- 60 forming an organic layer on the two metal wires of the metal layer;
- forming an indium tin oxide layer on the organic layer;
- coating a photoresist layer;
- performing an exposure step to the photoresist layer by utilizing a photo mask, the photo mask having a transparent area corresponding to a position between the two metal wires, an opaque material disposed in the transparent area, wherein

a width of the opaque material is less than a width of the transparent area of the photo mask;

performing a development step to the photoresist layer; and
performing an etching step to remove a part of the indium tin oxide layer and a part of the organic layer.

After the step of performing the etching step to remove the part of the indium tin oxide layer and the part of the organic layer, the method for preventing the short circuit between the metal wires in the organic light emitting diode display device of the present invention further comprises a step of:

stripping a remaining part of the photoresist layer.

In the method for preventing the short circuit between the metal wires in the organic light emitting diode display device of the present invention, the width of the opaque material is less than 2 μm .

In the method for preventing the short circuit between the metal wires in the organic light emitting diode display device of the present invention, the width of the opaque material is preferably ranging from 1 μm to 2 μm .

In the method for preventing the short circuit between the metal wires in the organic light emitting diode display device of the present invention, the two metal wires are utilized as sources.

In the method for preventing the short circuit between the metal wires in the organic light emitting diode display device of the present invention, the two metal wires are utilized as drains.

In the method for preventing the short circuit between the metal wires in the organic light emitting diode display device of the present invention, the organic layer at least covers a part of the two metal wires.

In the method for preventing the short circuit between the metal wires in the organic light emitting diode display device of the present invention, the two metal wires are formed by a wet etching method.

Comparing with the prior arts, by disposing the opaque material of which the width is less than the width of the transparent area, the method for preventing the short circuit between the metal wires in the organic light emitting diode display device of the present invention is capable of decreasing the thickness of the organic layer after the etching step is performed. As a result, the indium tin oxide layer can be removed completely, and the short circuit between the metal wires can be prevented.

For a better understanding of the aforementioned content of the present invention, preferable embodiments are illustrated in accordance with the attached figures for further explanation:

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 illustrates a top view of some elements of a conventional organic light emitting diode display device;

FIG. 2 illustrates a cross-sectional view along a line AA' in FIG. 1;

FIG. 3 illustrates a flow chart of a method for preventing a short circuit between metal wires in an organic light emitting diode display device in accordance with an embodiment of the present invention;

FIG. 4 illustrates a top view of some elements of the organic light emitting diode display device in accordance with the embodiment of the present invention;

FIG. 5 illustrates a top view after the method of the present invention is implemented in FIG. 4; and

FIG. 6 illustrates a cross-sectional view along a line BB' in FIG. 5.

DETAILED DESCRIPTION OF THE INVENTION

The following descriptions for the respective embodiments are specific embodiments capable of being implemented for illustrations of the present invention with referring to appended figures. For example, the terms of up, down, front, rear, left, right, interior, exterior, side, etcetera are merely directions of referring to appended figures. Therefore, the wordings of directions are employed for explaining and understanding the present invention but not limitations thereto.

Please refer to FIG. 3 to FIG. 6. FIG. 3 illustrates a flow chart of a method for preventing a short circuit between metal wires in an organic light emitting diode display device in accordance with an embodiment of the present invention. FIG. 4 illustrates a top view of some elements of the organic light emitting diode display device in accordance with the embodiment of the present invention. FIG. 5 illustrates a top view after the method of the present invention is implemented in FIG. 4. FIG. 6 illustrates a cross-sectional view along a line BB' in FIG. 5.

In step S300, a substrate 410 is provided.

In step S302, a gate layer (not shown) and a semiconductor layer (not shown) are formed on the substrate 410.

It is noted that since formation methods of the gate layer (not shown) and the semiconductor layer (not shown) are the same as those in the prior arts and are not key points of the present invention, they are not shown in FIG. 4 to FIG. 6.

In step S304, an inorganic layer 400 is formed on the substrate 410. It is noted that an area of the inorganic layer 400 formed on the substrate 410 is different from an area of the gate layer (not shown) and the semiconductor layer (not shown) formed on the substrate 410.

In step 306, a metal layer is formed on the inorganic layer 400, and the metal layer comprises at least two metal wires 402 and 404 which are served as sources or drains. The metal wires 402 and 404 are respectively utilized for transmitting independent signals, that is, for transmitting different signals.

The two metal wires 402 and 404 are, for example, but are not limited to, formed by a wet etching method.

In step S308, an organic layer 406 is formed on the metal wires 402 and 404 of the metal layer. The organic layer 406 at least covers a part of the metal wire 402 and a part of the metal wire 404. The organic layer 406 and the inorganic layer 400 are utilized as insulating layers and have a flat function for improving quality of manufacturing an organic light emitting diode in the following process.

In step S310, an indium tin oxide (ITO) layer 408 is formed on the organic layer 406. The indium tin oxide layer 408 is utilized as an anode of the organic light emitting diode.

It is noted that a position of the light emitting diode is formed in a light emitting area (not shown) of the substrate 410, and FIG. 4 and FIG. 5 illustrates a thin film transistor area. The indium tin oxide layer 408 (utilized as the anode of the light emitting diode) is required to be formed only in the light emitting area (not shown), and the indium tin oxide layer 408 is not required to be formed in the thin film transistor area. Accordingly, the indium tin oxide layer 408 in the thin film transistor area is required to be removed.

Step S310 further comprises the following step: a photoresist layer (not shown) is coated.

In step S312, an exposure step is performed to the photoresist layer (not shown) by utilizing a photo mask (not shown). The photo mask (not shown) has a transparent area C

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corresponding to a position between the metal wires **402** and **404**. An opaque material **420** is disposed in the transparent area C. A width W1 of the opaque material **420** is less than a width W2 of the transparent area C of the photo mask (not shown). The width W2 of the transparent area C is a resolution of the photo mask (not shown), that is, a resolution of an exposing machine. The transparent area C and the opaque material **420** are corresponding to a part of the inorganic layer **400** and a part of the organic layer **406**.

Taking an exposing machine of Canon Kabushiki Kaisha for example, the resolution is 2.5 μm (micrometer). Accordingly, the width W1 of the opaque material **420** should be designed in a range from 0 μm to 2 μm . After experimental verification, the width W1 of the opaque material **420** is preferably ranging from 1 μm to 2 μm .

In step S314, a development step is performed to the photoresist layer (not shown).

In step S316, an etching step is performed to remove a part of the indium tin oxide layer **408** and a part of the organic layer **406**. Since the width W1 of the opaque material **420** is less than the width W2 of the transparent area C, the organic layer **406** corresponding to an area between the transparent area C and the opaque material **420** is removed after the etching step. A removed part is shown as a dotted line area in FIG. 6. The organic layer **406** corresponding to an area of the opaque area **420** is not removed.

As shown in FIG. 6, since a thickness of the organic layer **406** in a border between the organic layer **406** and the inorganic layer **400** is decreased (that is, the dotted line area is removed), shadowing effect of the organic layer **406** does not occur. The indium tin oxide layer **408** can be irradiated by light, and thus the indium tin oxide layer **408** can be removed completely. The indium tin oxide **408** in the border between the inorganic layer **400** and the organic layer **406** is not left, thereby preventing a short circuit between the metal wires **402** and **404** in FIG. 4.

In step S318, a remaining part of the photoresist layer is stripped.

In step S320, a light emitting layer (not shown) and a cathode (now shown) are formed on the indium tin oxide layer in the light emitting area (not shown) in sequence for finishing the manufacturing of the organic light emitting diode.

It is noted that since formation methods of the light emitting layer (not shown) and the cathode (not shown) are not key points of the present invention, they are not shown in FIG. 4 to FIG. 6.

By disposing the opaque material **420** of which the width W1 is less than the width W2 of the transparent area C (step S314), the present invention is capable of decreasing the thickness of the organic layer **406** as shown in FIG. 6 after the etching step is performed to remove a part of the indium tin oxide layer **408** and a part of the organic layer **406** (step S320). As a result, the indium tin oxide layer **408** can be removed completely, and the short circuit between the metal wires **402** and **404** can be prevented.

As is understood by a person skilled in the art, the foregoing preferred embodiments of the present invention are illustrative rather than limiting of the present invention. It is intended that they cover various modifications and similar arrangements be included within the spirit and scope of the appended claims, the scope of which should be accorded the broadest interpretation so as to encompass all such modifications and similar structure.

What is claimed is:

1. A method for preventing a short circuit between metal wires in an organic light emitting diode display device, comprising:

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forming an inorganic layer on a substrate;

forming a metal layer on the inorganic layer, the metal layer comprising at least two metal wires;

forming an organic layer on the two metal wires of the metal layer;

forming an indium tin oxide layer on the organic layer;

coating a photoresist layer;

performing an exposure step to the photoresist layer by utilizing a photo mask, the photo mask having a transparent area corresponding to a position between the two metal wires, an opaque material disposed in the transparent area, wherein a width of the transparent area of the photo mask is a resolution of the photo mask, and a width of the opaque material is less than the width of the transparent area of the photo mask;

performing a development step to the photoresist layer; and performing an etching step to remove a part of the indium tin oxide layer and a part of the organic layer.

2. The method for preventing the short circuit between the metal wires in the organic light emitting diode display device of claim 1, further comprising a step of stripping a remaining part of the photoresist layer after the step of performing the etching step to remove the part of the indium tin oxide layer and the part of the organic layer.

3. The method for preventing the short circuit between the metal wires in the organic light emitting diode display device of claim 1, wherein the width of the opaque material is less than 2 μm .

4. The method for preventing the short circuit between the metal wires in the organic light emitting diode display device of claim 3, wherein the width of the opaque material is preferably ranging from 1 μm to 2 μm .

5. The method for preventing the short circuit between the metal wires in the organic light emitting diode display device of claim 1, wherein the two metal wires are utilized as sources.

6. The method for preventing the short circuit between the metal wires in the organic light emitting diode display device of claim 1, wherein the two metal wires are utilized as drains.

7. The method for preventing the short circuit between the metal wires in the organic light emitting diode display device of claim 1, wherein the organic layer at least covers a part of the two metal wires.

8. The method for preventing the short circuit between the metal wires in the organic light emitting diode display device of claim 1, wherein the two metal wires are formed by a wet etching method.

9. A method for preventing a short circuit between metal wires in an organic light emitting diode display device, comprising:

forming an inorganic layer on a substrate;

forming a metal layer on the inorganic layer, the metal layer comprising at least two metal wires;

forming an organic layer on the two metal wires of the metal layer;

forming an indium tin oxide layer on the organic layer;

coating a photoresist layer;

performing an exposure step to the photoresist layer by utilizing a photo mask, the photo mask having a transparent area corresponding to a position between the two metal wires, an opaque material disposed in the transparent area, wherein a width of the opaque material is less than a width of the transparent area of the photo mask;

performing a development step to the photoresist layer; and performing an etching step to remove a part of the indium tin oxide layer and a part of the organic layer.

10. The method for preventing the short circuit between the metal wires in the organic light emitting diode display device of claim 9, further comprising a step of stripping a remaining part of the photoresist layer after the step of performing the etching step to remove the part of the indium tin oxide layer and the part of the organic layer. 5

11. The method for preventing the short circuit between the metal wires in the organic light emitting diode display device of claim 9, wherein the width of the opaque material is less than 2 μm . 10

12. The method for preventing the short circuit between the metal wires in the organic light emitting diode display device of claim 11, wherein the width of the opaque material is preferably ranging from 1 μm to 2 μm .

13. The method for preventing the short circuit between the metal wires in the organic light emitting diode display device of claim 9, wherein the two metal wires are utilized as sources. 15

14. The method for preventing the short circuit between the metal wires in the organic light emitting diode display device of claim 9, wherein the two metal wires are utilized as drains. 20

15. The method for preventing the short circuit between the metal wires in the organic light emitting diode display device of claim 9, wherein the organic layer at least covers a part of the two metal wires. 25

16. The method for preventing the short circuit between the metal wires in the organic light emitting diode display device of claim 9, wherein the two metal wires are formed by a wet etching method. 30

* * * * *

专利名称(译)	防止有机发光二极管显示装置中的金属线之间短路的方法		
公开(公告)号	US9076992	公开(公告)日	2015-07-07
申请号	US14/129992	申请日	2013-11-28
[标]申请(专利权)人(译)	深圳市华星光电技术有限公司		
申请(专利权)人(译)	深圳中星光电科技有限公司		
当前申请(专利权)人(译)	深圳市中国星光电科技有限公司.		
[标]发明人	KO KAI YUAN		
发明人	KO, KAI-YUAN		
IPC分类号	H01L27/32 H01L51/56		
CPC分类号	H01L51/56 H01L27/3276 H01L2251/5392 H01L2227/323 H01L27/1244 H01L27/1288 H01L27/3258		
审查员(译)	迪亚洛MAMADOU		
优先权	201310361689.6 2013-08-19 CN		
其他公开文献	US20150140714A1		
外部链接	Espacenet USPTO		

摘要(译)

公开了一种用于防止有机发光二极管显示装置中的金属线之间的短路的方法。该方法包括：在基板上形成无机层；在无机层上形成包括两根金属线的金属层；在两根金属线上形成有机层；在有机层上形成氧化铟锡层；涂覆光刻胶层；通过利用具有透明区域的光掩模，设置在透明区域中的不透明材料进行曝光步骤，其中不透明材料的宽度小于透明区域的宽度；对光致抗蚀剂层进行显影步骤；并且执行蚀刻步骤以去除部分氧化铟锡层和部分有机层。本发明可以防止金属线之间的短路。

